

Vishay Siliconix

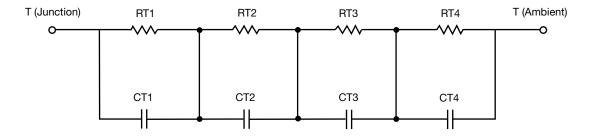
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot			
RT1	N/A	2.7355	N/A			
RT2	N/A	1.04	N/A			
RT3	N/A	124.3817m	N/A			
RT4	N/A	376.0282m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	N/A	2.2943	N/A			
CT2	N/A	419.0977m	N/A			
CT3	N/A	605.4822u	N/A			
CT4	N/A	32.2092m	N/A			

Note

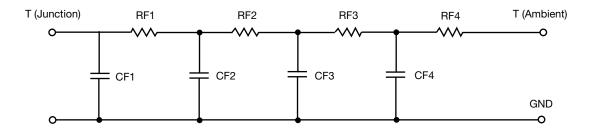
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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R-C THERMAL MODEL FOR FILTER CONFIGURATION



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	144.1767m	N/A		
RF2	N/A	445.2913m	N/A		
RF3	N/A	1.4712	N/A		
RF4	N/A	2.5354	N/A		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	656.3309u	N/A		
CF2	N/A	34.0248m	N/A		
CF3	N/A	356.2821m	N/A		
CF4	N/A	2.7751	N/A		

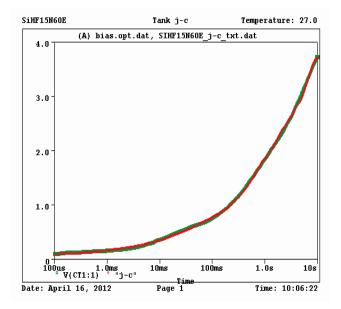
Note

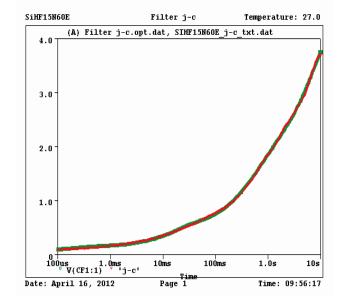
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SiHF15N60E_RC

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